

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

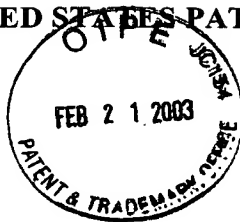
In re Application of

Katoh, T. et al.

Serial No.: 09/711,504

Filed: November 14, 2000

For: THIN FILM TRANSISTOR AND FABRICATION METHOD OF THE SAME



Group Art Unit: 2814

Examiner: Sefer, A.

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EXCESS CLAIM FEE PAYMENT LETTER

Sir:

Transmitted herewith is an amendment in the above-identified application. The fee has been calculated and is transmitted as shown below.

	<u>AFTER AMENDMENT</u>	<u>PREV. PAID FOR</u>	<u>EXTRA CLAIMS PRESENT</u>	<u>RATE</u>	<u>FEE DUE</u>
Total Claims	18 -	20	= 0	x \$18.00	\$.00
Indep. Claims	7 -	6	= 1	x \$84.00	\$ 84.00

TOTAL ADDITIONAL FEE FOR THIS AMENDMENT

\$ 84.00

A check in the amount of \$84.00 to cover the excess claim fees. A duplicate copy of this sheet is enclosed. The Commissioner is authorized charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

Respectfully Submitted,

Date:

2/21/03

Sean M. McGinn

Reg. No. 34,386

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

2826
#128
Amend.
S Davis
3/4/03

In re Application of

Katoh, T. et al.

Serial No.: 09/711,504 ✓

Group Art Unit: 2826

Filed: November 14, 2000

Examiner: Sefer, A.

For: THIN FILM TRANSISTOR AND FABRICATION METHOD ✓ OF THE SAME

Honorable Commissioner of Patents
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated October 21, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 17-23 without prejudice or disclaimer:

Please amend the claims as follows:

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- 1 4. (Amended) A thin film transistor including:
2 a back channel electrode,
3 wherein a voltage of a front channel positioned on the side of a gate wiring of said
4 thin film transistor is made equal to a voltage of said back channel positioned on the side of a
5 back channel electrode by short-circuiting said back channel electrode to a gate electrode
6 through a contact-hole provided in a portion of a semiconductor layer forming said thin film
7 transistor, and
8 wherein said contact-hole is formed in a location remote from an active region of said
9 thin film transistor by at least five microns.